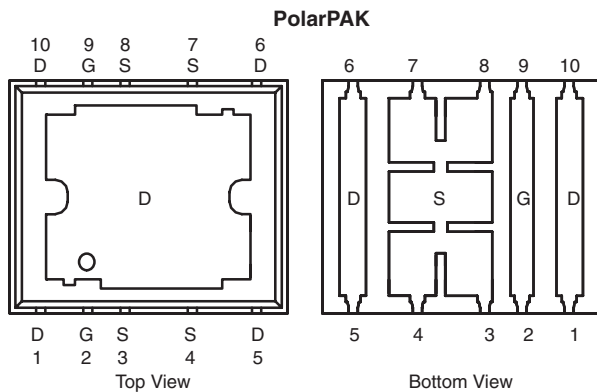


N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) ^e	I _D (A) ^a		Q _g (Typ.)
		Silicon Limit	Package Limit	
30	0.0019 at V _{GS} = 10 V	202	60	50 nC
	0.0026 at V _{GS} = 4.5 V	173	60	

Package Drawing
www.vishay.com/doc?72945



Top surface is connected to pins 1, 5, 6, and 10

Ordering Information: SiE802DF-T1-E3 (Lead (Pb)-free)
SiE802DF-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30		V
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	202 (Silicon Limit)	A
			60 ^a (Package Limit)	
		T _C = 70 °C	60 ^a	
		T _A = 25 °C	42.7 ^{b, c}	
Pulsed Drain Current	I _{DM}	T _A = 70 °C	34.2 ^{b, c}	
			100	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	60 ^a	
		T _A = 25 °C	4.3 ^{b, c}	
Single Pulse Avalanche Current	I _{AS}	50		
Avalanche Energy	E _{AS}	125		mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	125	W
		T _C = 70 °C	80	
		T _A = 25 °C	5.2 ^{b, c}	
		T _A = 70 °C	3.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

Notes:

- Package limited is 60 A.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (www.vishay.com/doc?73257). The PolarPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

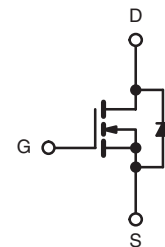
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Gen II Power MOSFET
- Ultra Low Thermal Resistance Using Top-Exposed PolarPAK[®] Package for Double-Sided Cooling
- Leadframe-Based New Encapsulated Package
 - Die Not Exposed
 - Same Layout Regardless of Die Size
- Low Q_{gd}/Q_{gs} Ratio Helps Prevent Shoot-Through
- 100 % R_g and UIS Tested
- Compliant to RoHS directive 2002/95/EC



APPLICATIONS

- VRM
- DC/DC Conversion: Low-Side
- Synchronous Rectification



N-Channel MOSFET
For Related Documents
www.vishay.com/ppg?72985

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	$t \leq 10$ s	R_{thJA}	20	24	°C/W
Maximum Junction-to-Case (Drain Top)	Steady State	R_{thJC} (Drain)	0.8	1	
Maximum Junction-to-Case (Source) ^{a, c}		R_{thJC} (Source)	2.2	2.7	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
b. Maximum under Steady State conditions is 68 °C/W.
c. Measured at source pin (on the side of the package).

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

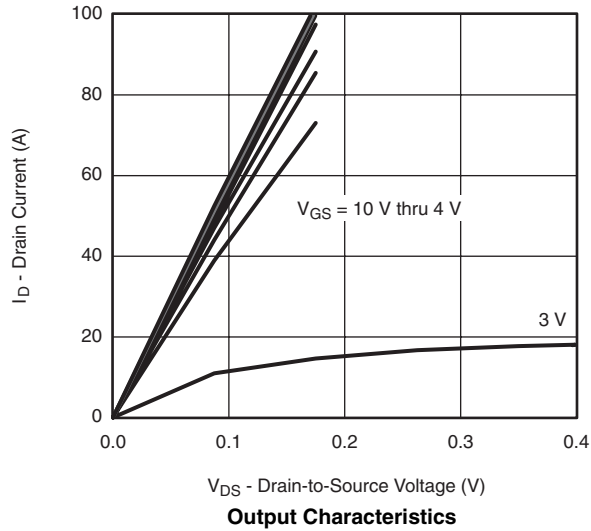
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ μ A		32.2		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-6.4			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μ A	1.5	2.2	2.7	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30$ V, $V_{GS} = 0$ V			1	μ A
		$V_{DS} = 30$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 10$ V	25			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 23.6$ A		0.0016	0.0019	Ω
		$V_{GS} = 4.5$ V, $I_D = 21.3$ A		0.0021	0.0026	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15$ V, $I_D = 23.6$ A		156		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15$ V, $V_{GS} = 0$ V, $f = 1$ MHz		7000		pF
Output Capacitance	C_{oss}		1200			
Reverse Transfer Capacitance	C_{rss}		500			
Total Gate Charge	Q_g	$V_{DS} = 15$ V, $V_{GS} = 10$ V, $I_D = 23.6$ A		105	160	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 15$ V, $V_{GS} = 4.5$ V, $I_D = 23.6$ A		50	75	
Gate-Drain Charge	Q_{gd}		21			
Gate Resistance	R_g	$f = 1$ MHz		1.1	1.65	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15$ V, $R_L = 1.5$ Ω $I_D \cong 10$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω		45	70	ns
Rise Time	t_r		195	300		
Turn-Off Delay Time	$t_{d(off)}$		45	70		
Fall Time	t_f		20	30		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15$ V, $R_L = 1.5$ Ω $I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ Ω		25	40	
Rise Time	t_r		20	30		
Turn-Off Delay Time	$t_{d(off)}$		65	100		
Fall Time	t_f		10	15		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C			60	A
Pulse Diode Forward Current ^a	I_{SM}				100	
Body Diode Voltage	V_{SD}	$I_S = 10$ A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10$ A, $di/dt = 100$ A/ μ s, $T_J = 25$ °C		55	85	ns
Body Diode Reverse Recovery Charge	Q_{rr}			66	105	nC
Reverse Recovery Fall Time	t_a			25		ns
Reverse Recovery Rise Time	t_b			30		

Notes:

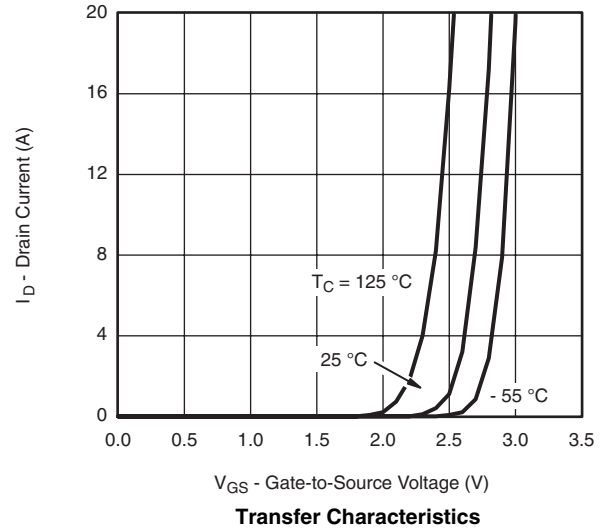
- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

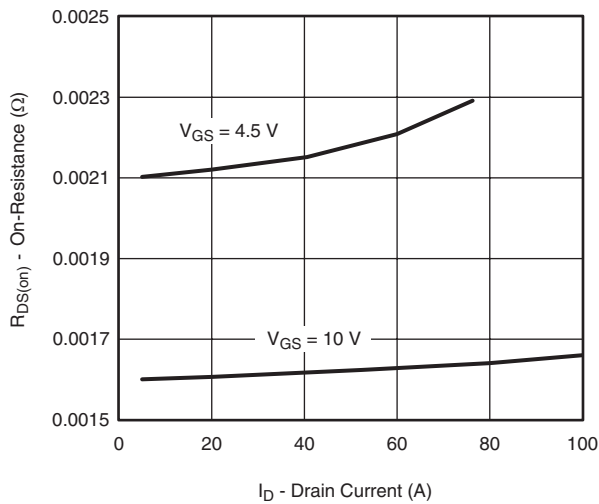
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



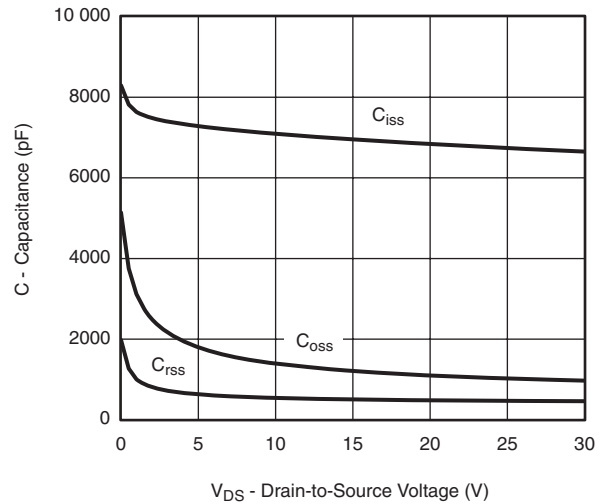
Output Characteristics



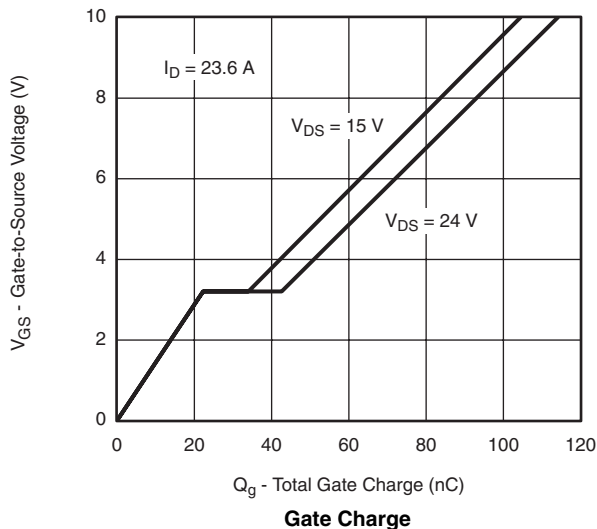
Transfer Characteristics



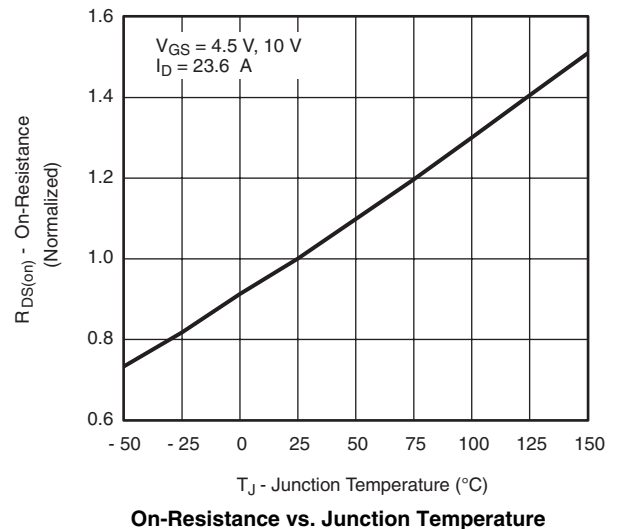
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

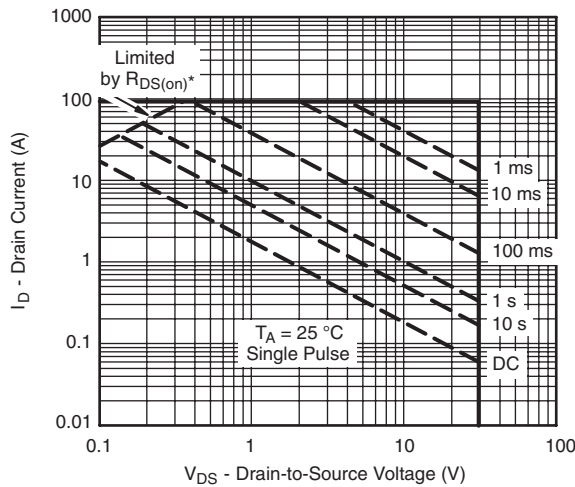
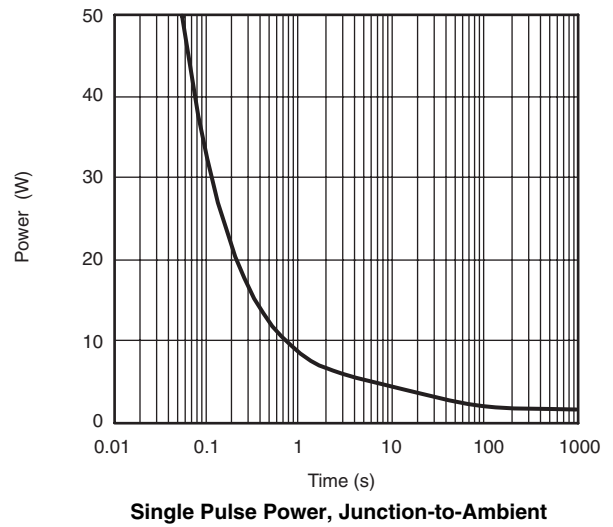
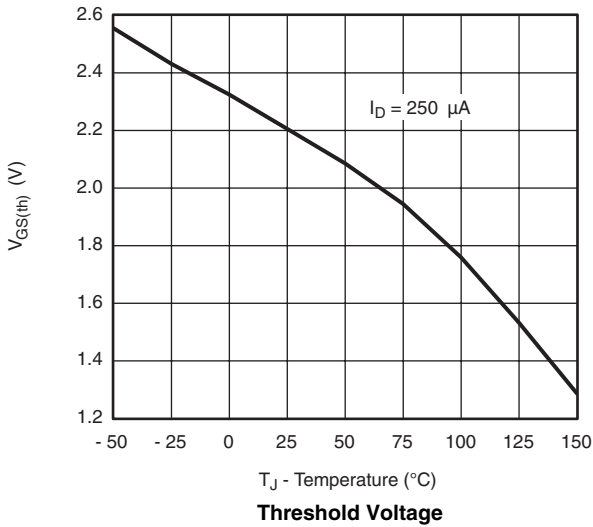
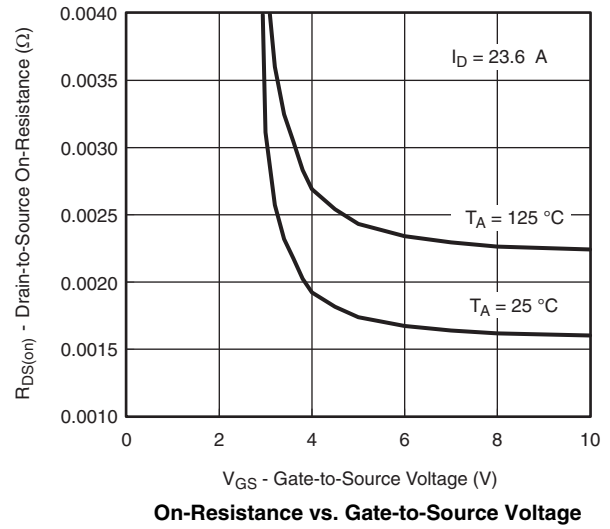
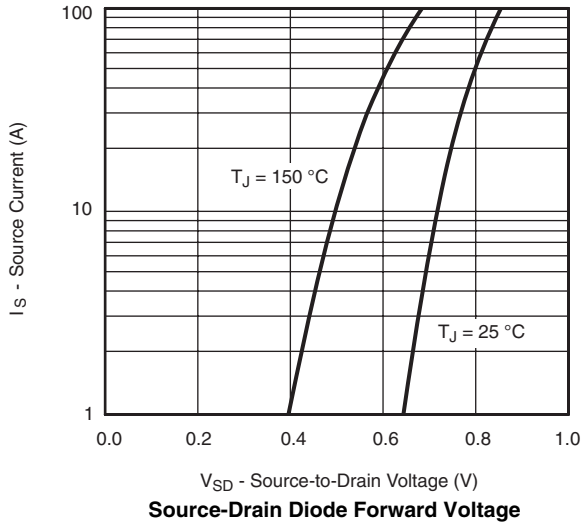


Gate Charge



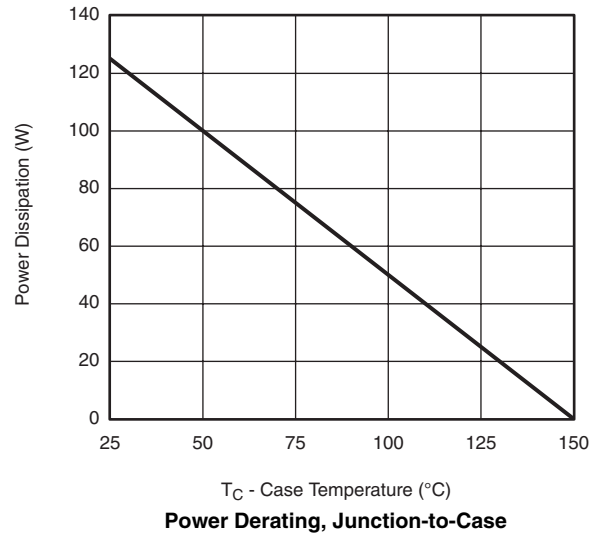
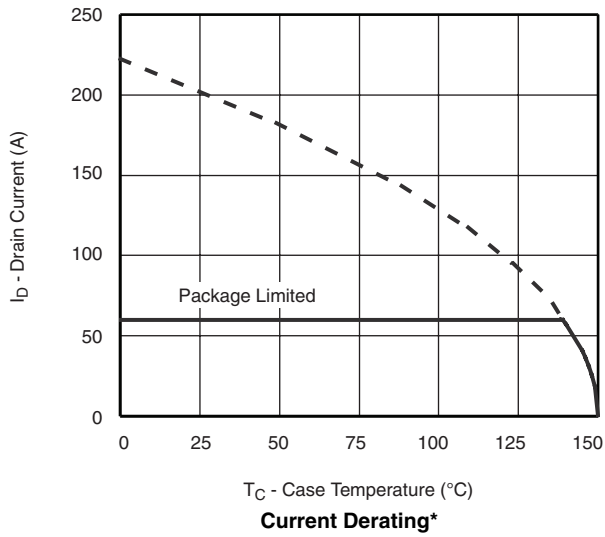
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



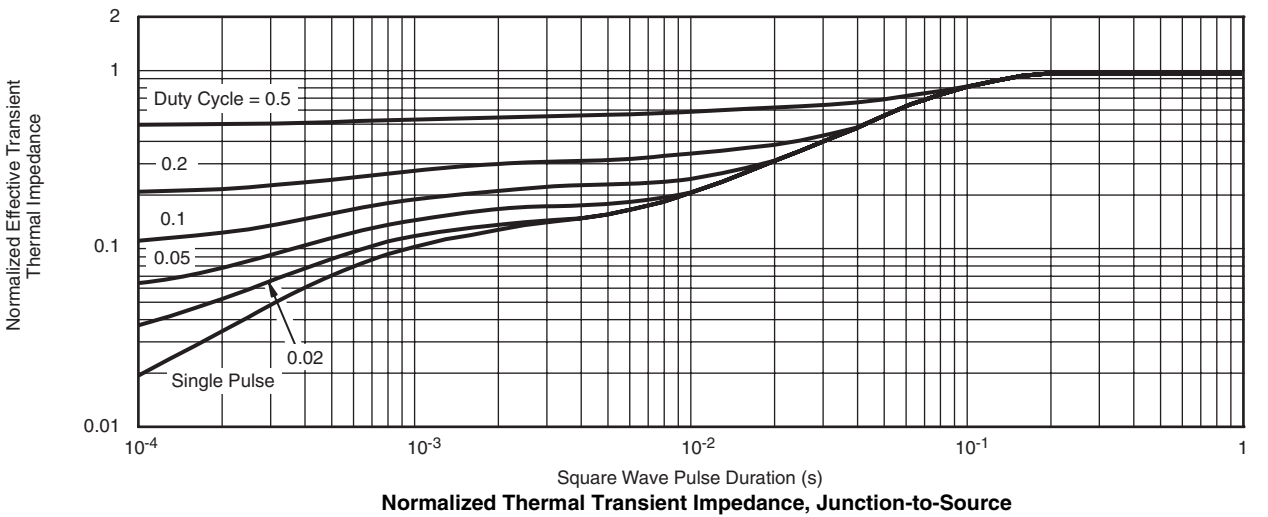
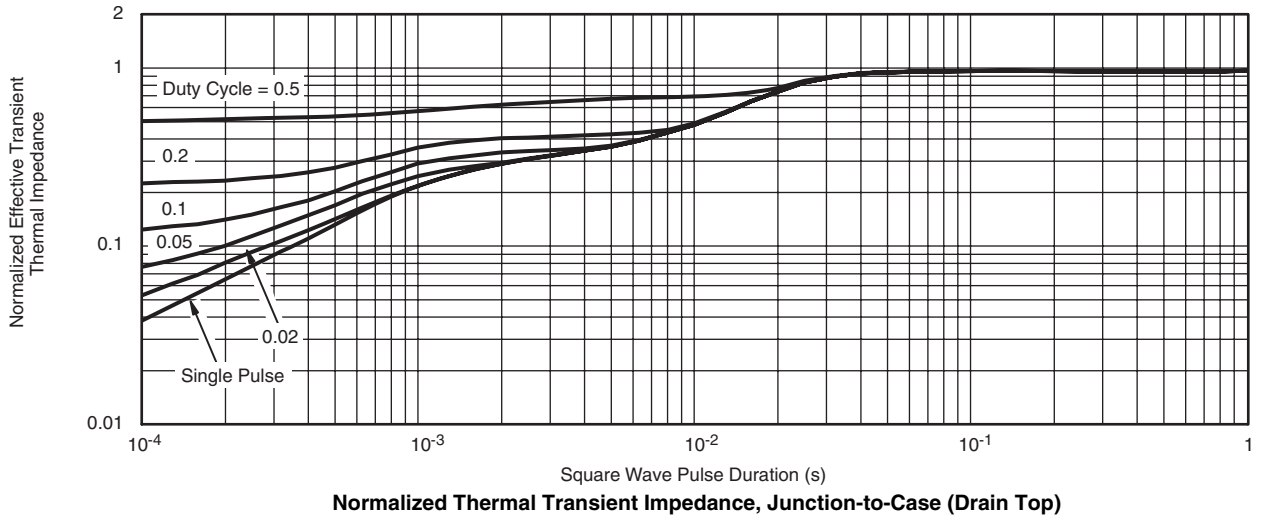
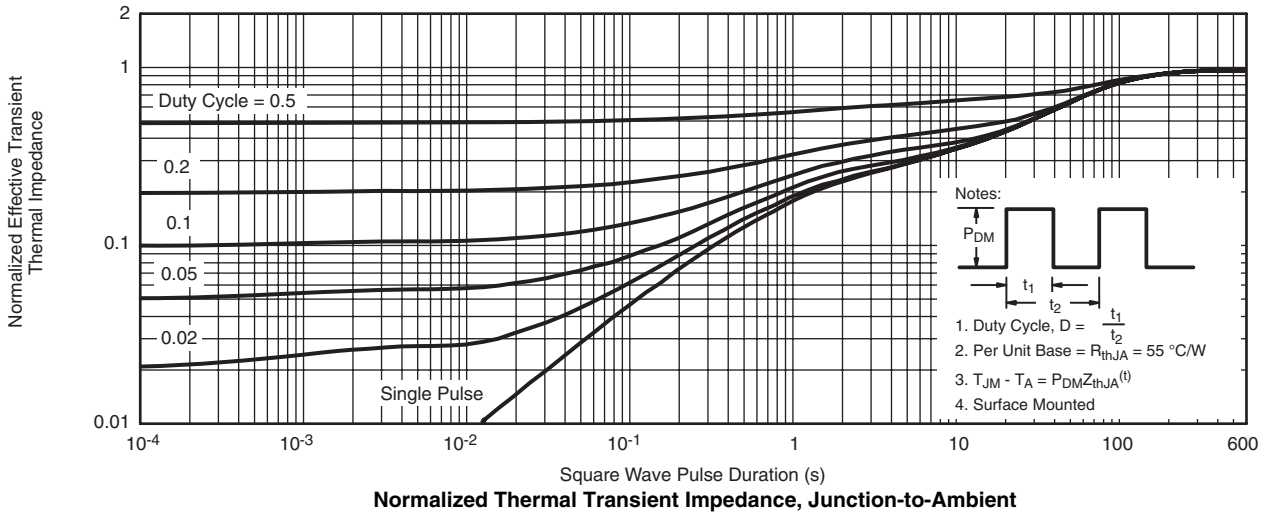
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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